PIN Diodes

Q: Just how do we **make** switches and voltage controlled attenuators?

A: Typically, they are constructed with PIN diodes.

A PIN diode is simply a *p-n* junction diode that is designed to have a very **small junction capacitance** (0.01 to 0.1 pf).

Sort of the **opposite** of the **varactor** diode!

To see why this is important, recall diode **small signal analysis** from your first electronics course.

In small signal analysis, the **total** diode voltage consists of a D.C. bias voltage (V_0) and a small, time-varying signal (v_d):

$$V_D(t) = \frac{V_0}{V_0} + \frac{V_d(t)}{V_d(t)}$$

For radio engineering applications, the small signal is a **microwave** signal !!! I.E.,:

$$\boldsymbol{v}_{D}(\boldsymbol{t}) = \boldsymbol{V}_{0} + \boldsymbol{v}_{RF}(\boldsymbol{t})$$

Thus, we know that the **diode current** i_D is:

$$\dot{V}_{D} = I_{s} \left(\exp \left[\frac{V_{0} + V_{RF}(t)}{n V_{T}} \right] - 1 \right)$$

2/5

Since v_{RF} is very small, we can approximate this diode current $i_D(v_D)$ using a Taylor Series expansion around $v_D = V_O$: $i_{D}(v_{D}) \approx i_{D}(v_{D})\Big|_{v_{D}=v_{D}} + \frac{\partial i_{D}(v_{D})}{\partial v_{D}}\Big|_{v_{D}=v_{D}} + \frac{\partial i_{D}(v_{D})}{\partial v_{D}}\Big|_{v_{D}=v_{D}} + \frac{v_{RF}(t)}{nv_{T}} + \frac{I_{S}e^{v_{D}/nv_{T}}}{nv_{T}} + \frac{I_{S}e^{v_{D}/nv_{T}}}{nv_{T}} + \frac{v_{RF}(t)}{nv_{T}} + \frac{v_{RF}(t)}{nv_{T}}$ We recognize that: $I_{\mathcal{S}}\left(e^{\frac{V_{0}}{nV_{T}}}-1\right)=\mathsf{D}.\mathsf{C}.$ Bias Current \doteq I_{0} and thus we can write our small-signal approximation as: $\dot{I}_{D} = I_{0} + \frac{(I_{0} + I_{s})}{nV_{T}} V_{RF}(t)$ $=I_0+\frac{V_{RF}(t)}{r_{a}}$ where we have defined the diode small-signal resistance r_d as: $r_d = \frac{nV_T}{I_0 + I_1}$ The diode small-signal resistance is also often referred to as

the junction resistance R_j or the series resistance R_s .

We can further conclude that the total diode current i_D is the sum of the D.C. bias current I_O , and the small-signal current $i_{RF}(t)$, where:

$$i_{RF}(t) = \frac{v_{RF}(t)}{r_d}$$

Just like Ohm's Law !

To a small (i.e., low power) microwave signal, a diode "looks" like a **resistor**.

Moreover, we can **control** and **modify** the resistance of the diode by **changing** the D.C. **bias**.

Sort of a voltage-controlled resistor!

For example, if we put the diode into **forward** bias $(V_0 >> nV_{\tau})$, the bias current I_0 will be positive and **big**, thus the junction resistance will be very **small** (e.g., r_d = a few ohms).

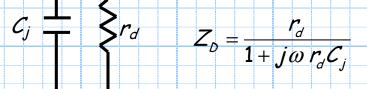
A forward biased diode is very nearly a microwave
 short circuit!

 $r_d = \frac{nV_T}{I_0 + I_s}$

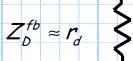
I get it! If we reverse bias our diode, such that $V_0 \ll -nV_T$, the bias current I_0 will be nearly equal to $-I_s$. As a result, the series resistance will be hugemungous! Not so fast! The small-signal resistance of a reverse biased diode is in fact very large. BUT, we must also consider the junction capacitance C_j !

Recall that in **reverse** bias, the junction capacitance of a diode can be **significant**, and in fact generally **increases** as the bias voltage becomes more negative!

As a result, a good microwave circuit **model** of a diode includes both the series resistance and junction capacitance:



For forward bias, where r_d is very small, we find that diode impedance Z_D is approximately equal to this small series resistance $(Z_D \approx r_d)$ —a short circuit (approximately):



For reverse bias, where r_d is **very large**, we find that diode impedance Z_D is approximately equal to that of the junction **capacitance** C_j :

For low-frequencies (e.g., kHz), this impedance will be typically be **very** large and thus the diode can be approximate as an **open** circuit.

 $Z_D^{rb} = \frac{\mathbf{I}}{j\omega C_j}$

However, at microwave frequencies (where ω is very large) the reverse bias impedance Z_{D}^{rb} may **not** be particularly large, and thus the reverse biased diode **cannot** be considered an open circuit.

In order for the impedance $Z_D^{rb} = 1/j\omega C_j$ to be very large at **microwave** frequencies, the junction capacitance C_j must be very, very small.



PIN diodes! I **bet** that's why we use **PIN** diodes!

That's **exactly** why! A PIN diode is approximately a (bias) voltage controlled resistor at microwave frequencies. We can select any value of r_d from a short to an open.

As a result, we can make **many** interesting devices!